

**SEMICONDUCTOR LASER DEVICE AND METHOD FOR FABRICATING
THE SAME**

ABSTRACT OF DISCLOSURE

A method for fabricating a buried semiconductor laser device including the steps of: forming a mesa structure including a bottom cladding layer, an active layer and a top cladding layer overlying an n-type semiconductor substrate; and forming a current confinement structure by growing a p-type current blocking layer and an n-type current blocking layer on each side surface of the mesa structure and on a skirt portion extending from the each side surface, the p-type current blocking layer being fabricated by using a raw material gas containing a group III element gas and a group V element gas at a molar ratio between 60 and 350 inclusive. In this method, the semiconductor laser device including the current confinement structure with the specified leakage current path width can be fabricated with the excellent reproducibility.